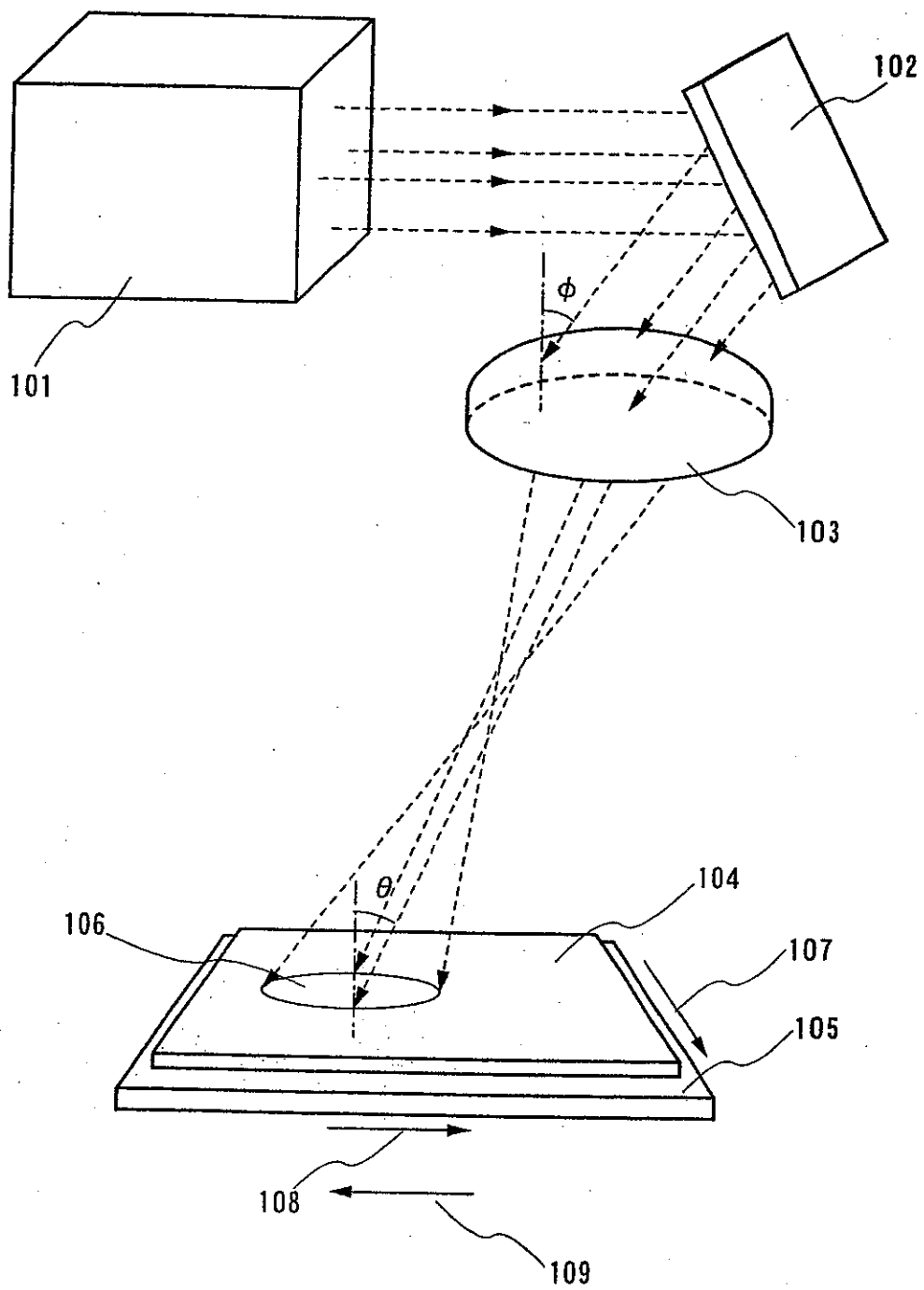


Fig. 1



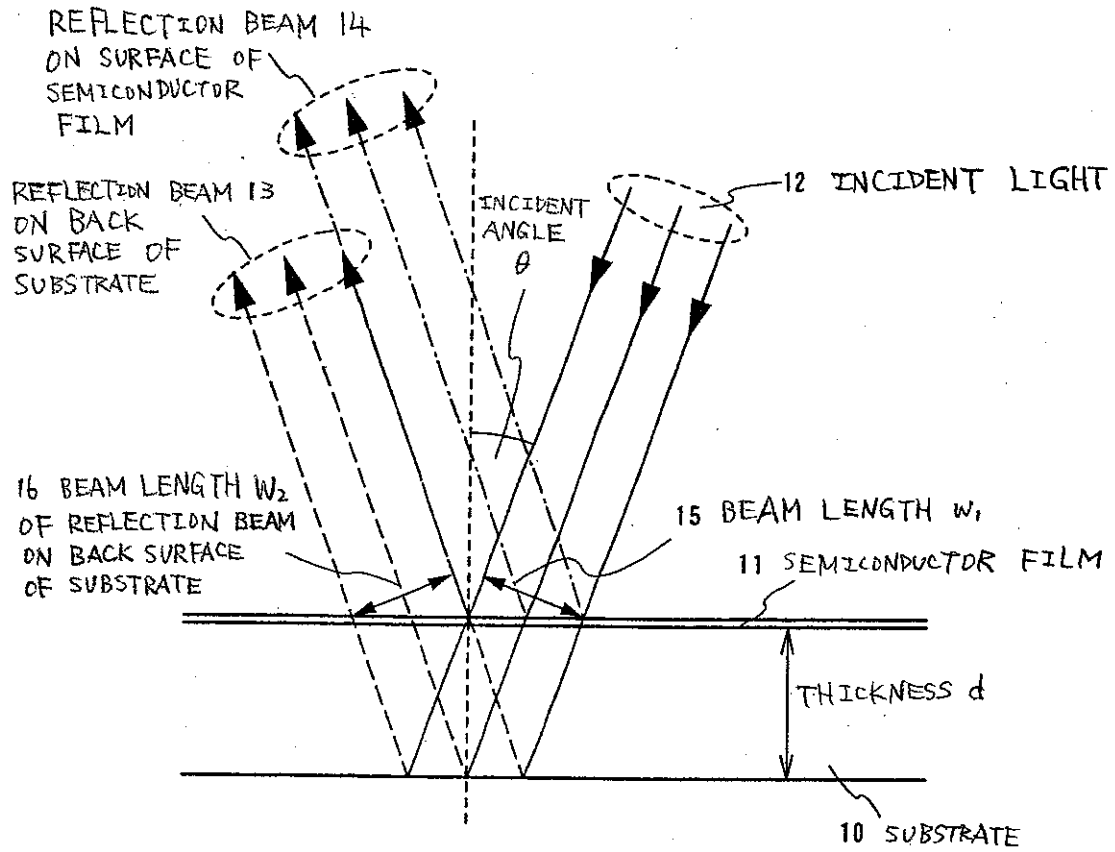


Fig.2

3/28

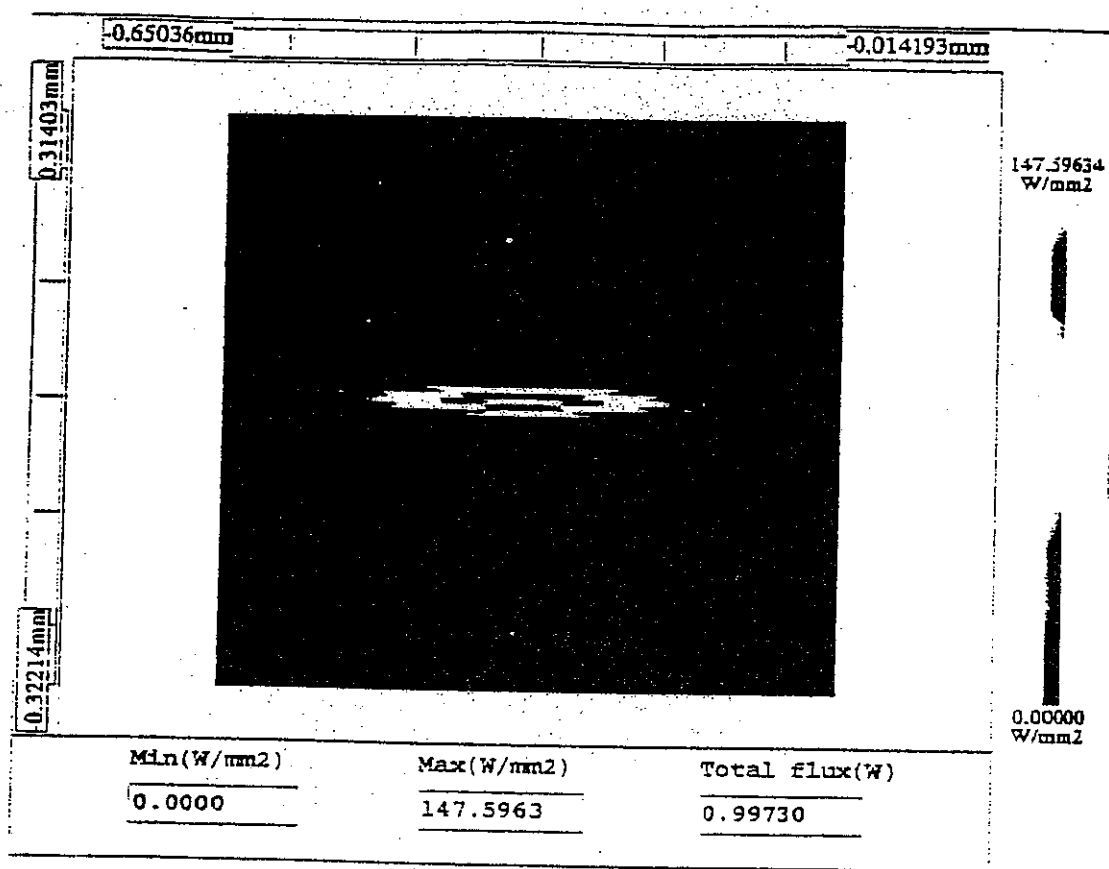
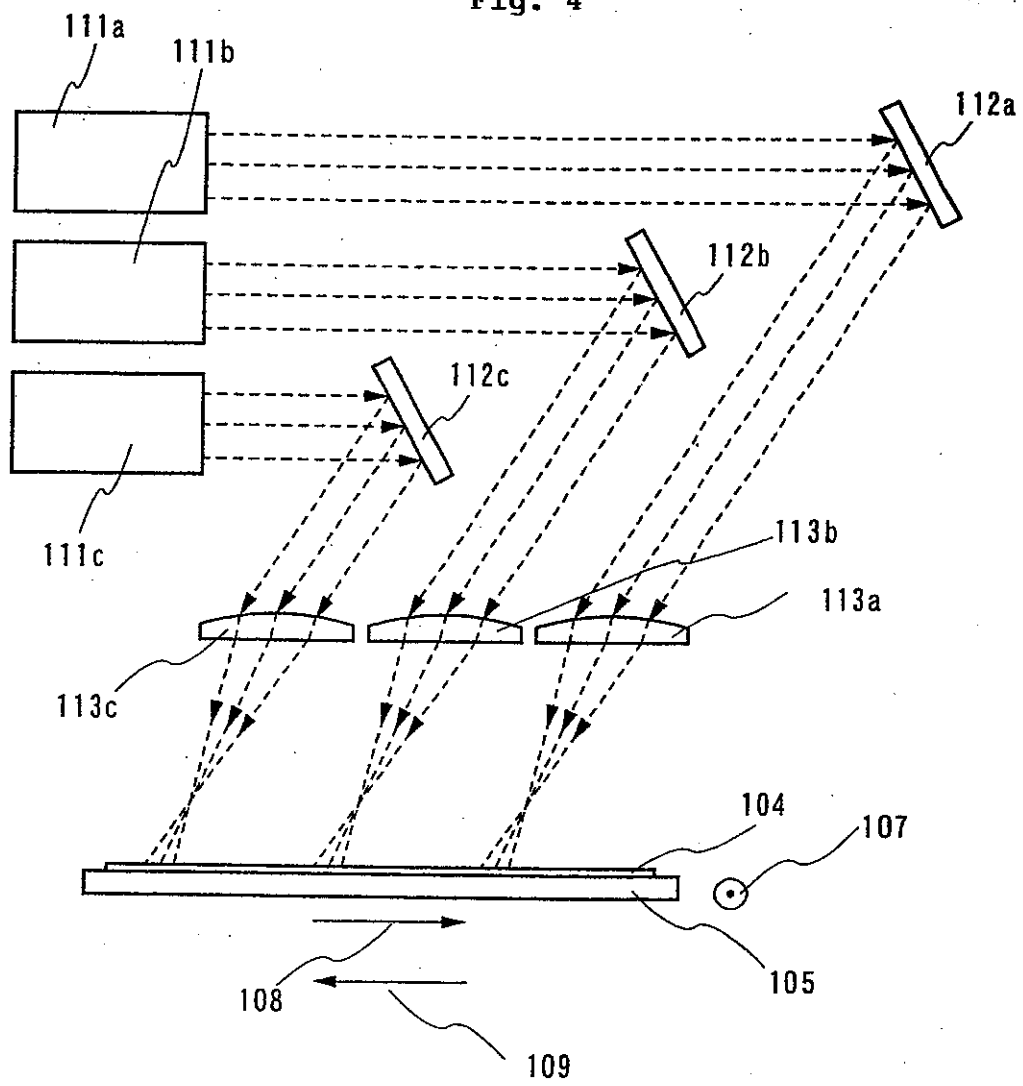


Fig.3

Fig. 4



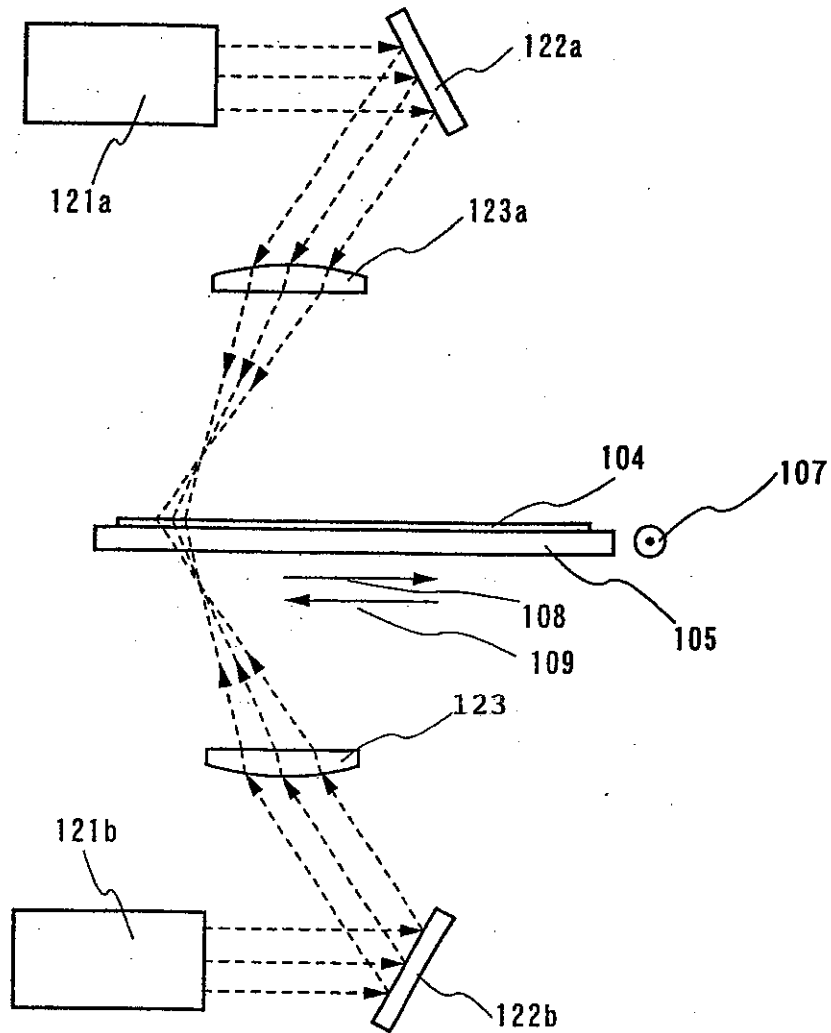


Fig. 5

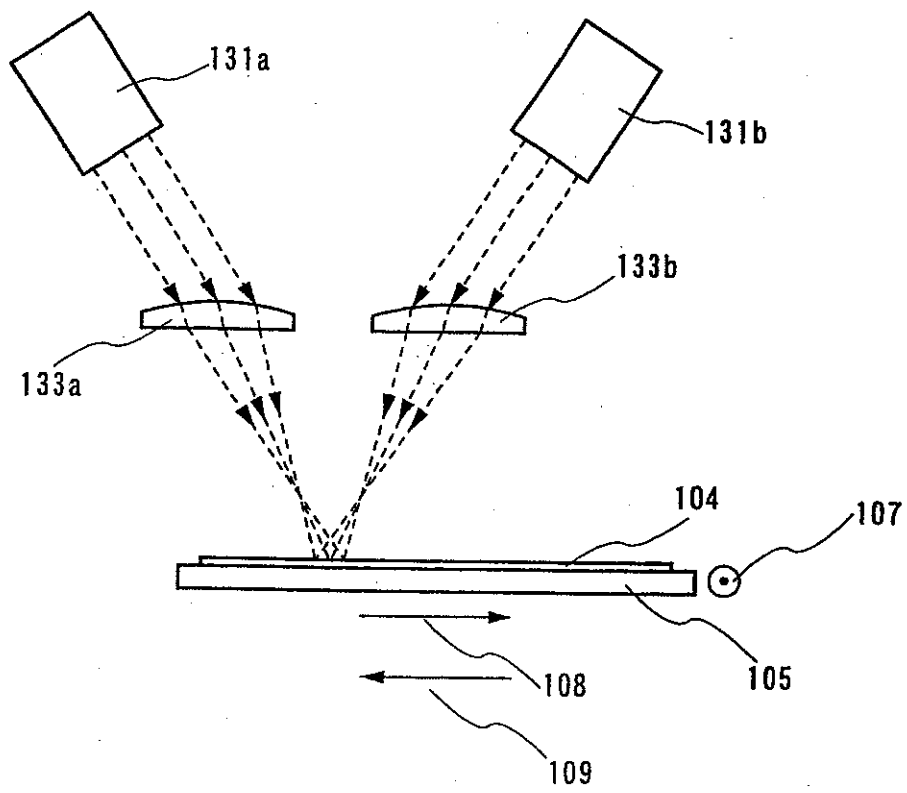
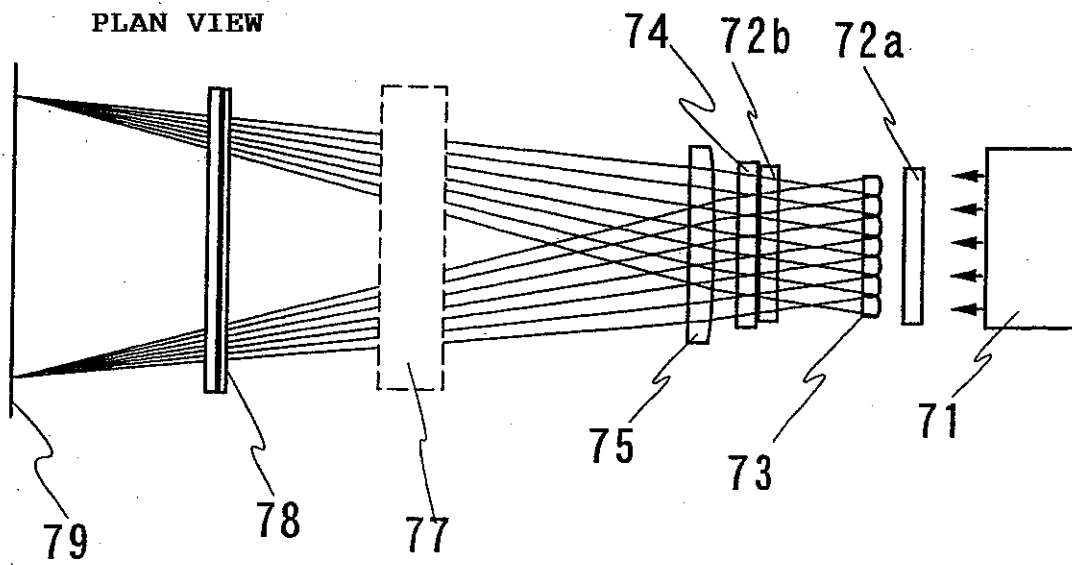
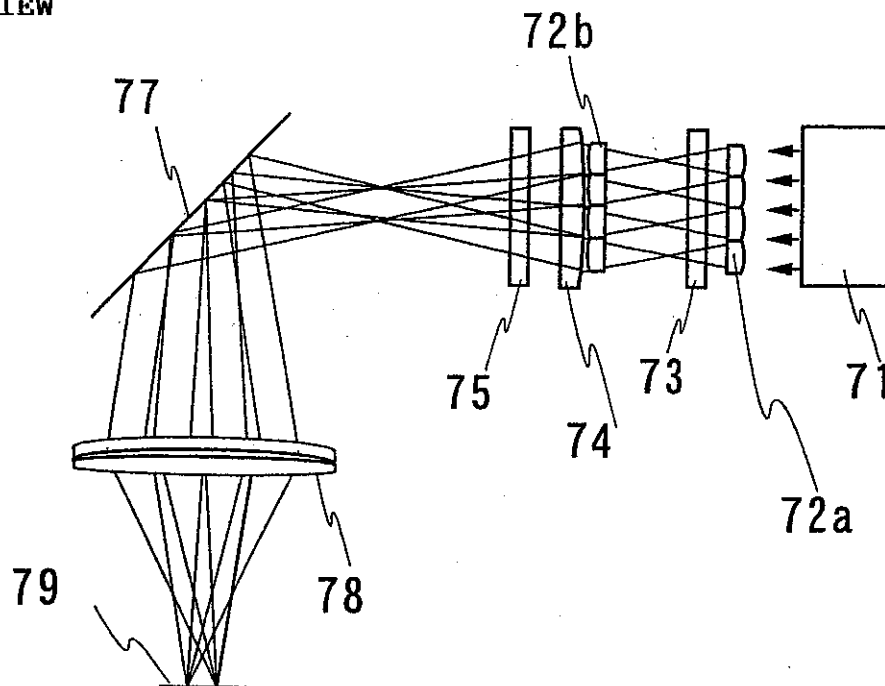


Fig.6

Fig. 7

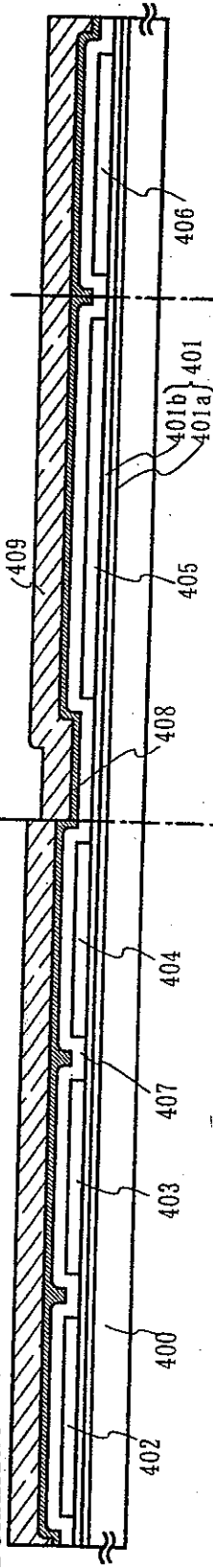


SIDE VIEW



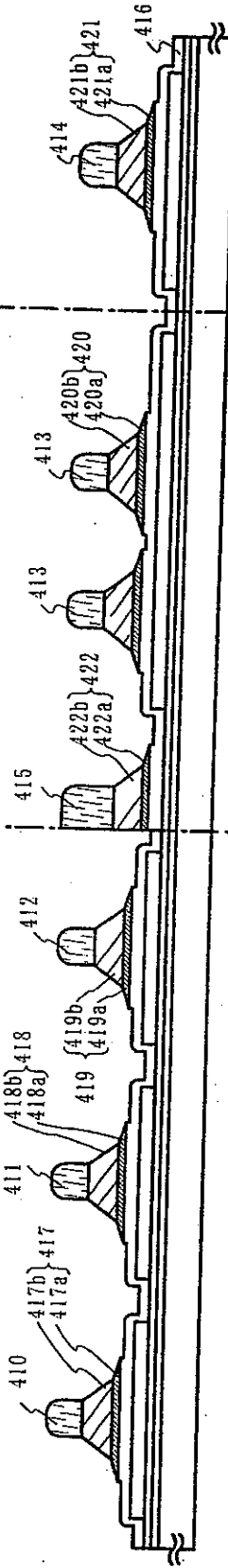
FORMATION OF BASE FILM/FORMATION OF SEMICONDUCTOR LAYER/FORMATION OF INSULATING FILM/
FORMATION OF FIRST CONDUCTIVE FILM AND SECOND CONDUCTIVE FILM

Fig. 8A



FIRST ETCHING PROCESS

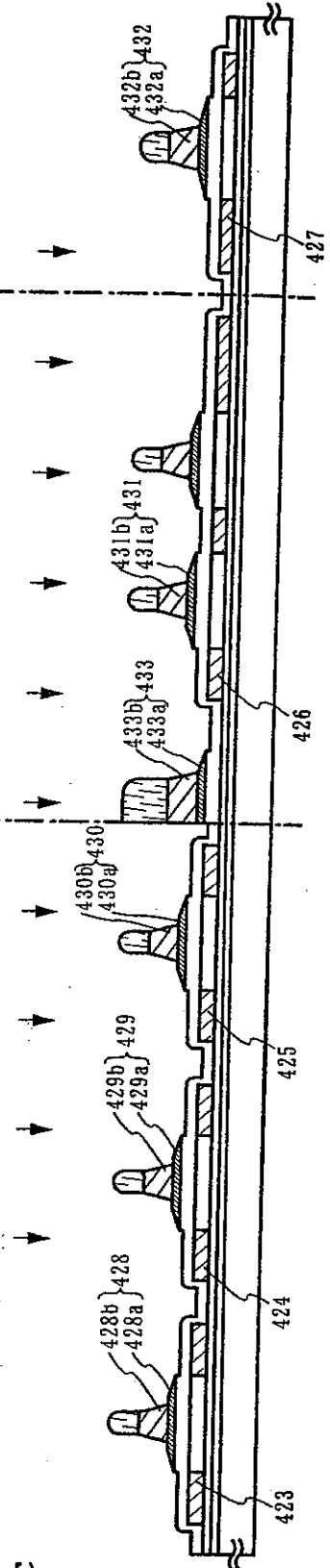
Fig. 8B



SECOND ETCHING PROCESS

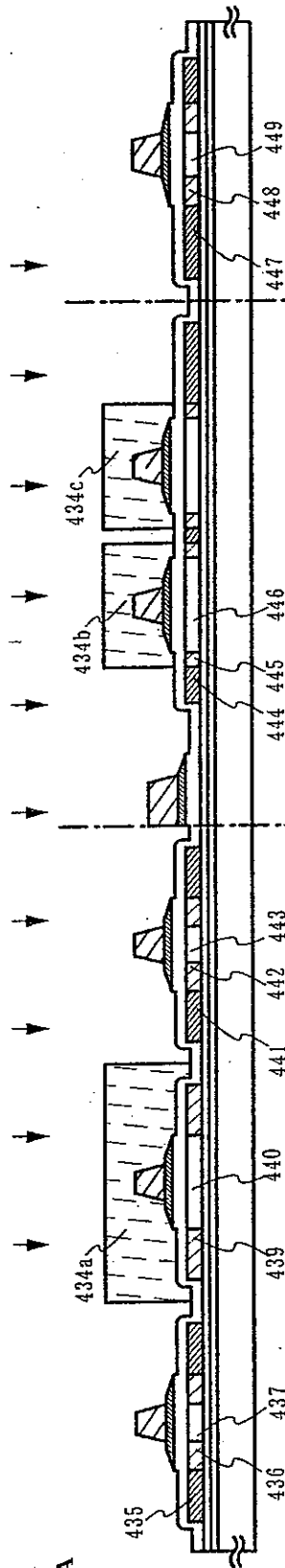
FIRST DOPING PROCESS

Fig. 8C



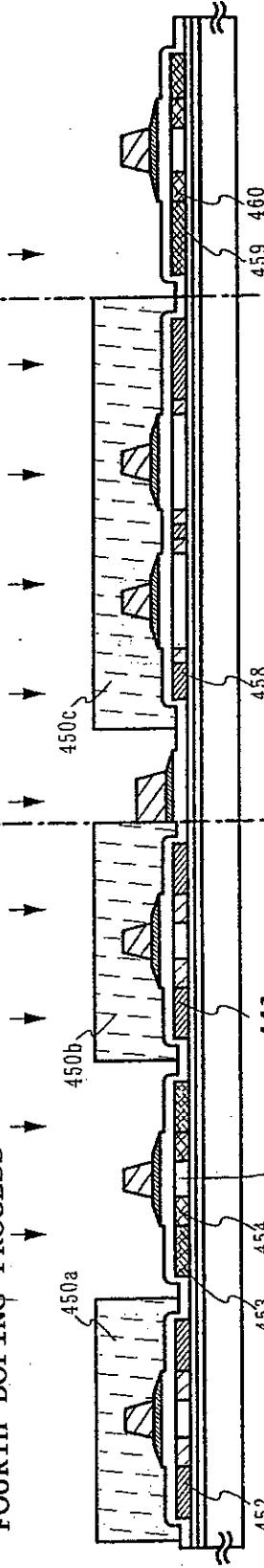
SECOND DOPING PROCESS/THIRD DOPING PROCESS

Fig. 9A



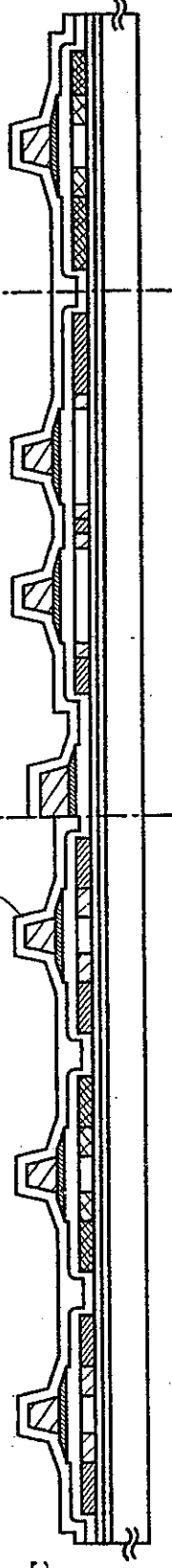
FOURTH DOPING PROCESS

Fig. 9B



FORMATION OF FIRST INTERLAYER INSULATING FILM/LASER BEAM IRRADIATION/HEAT TREATMENT

Fig. 9C



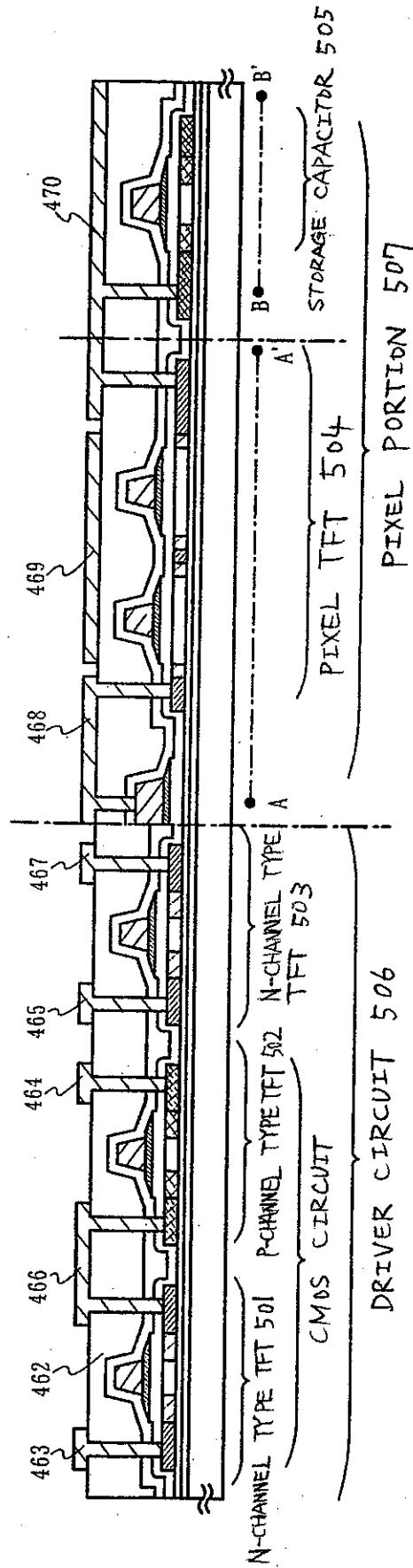
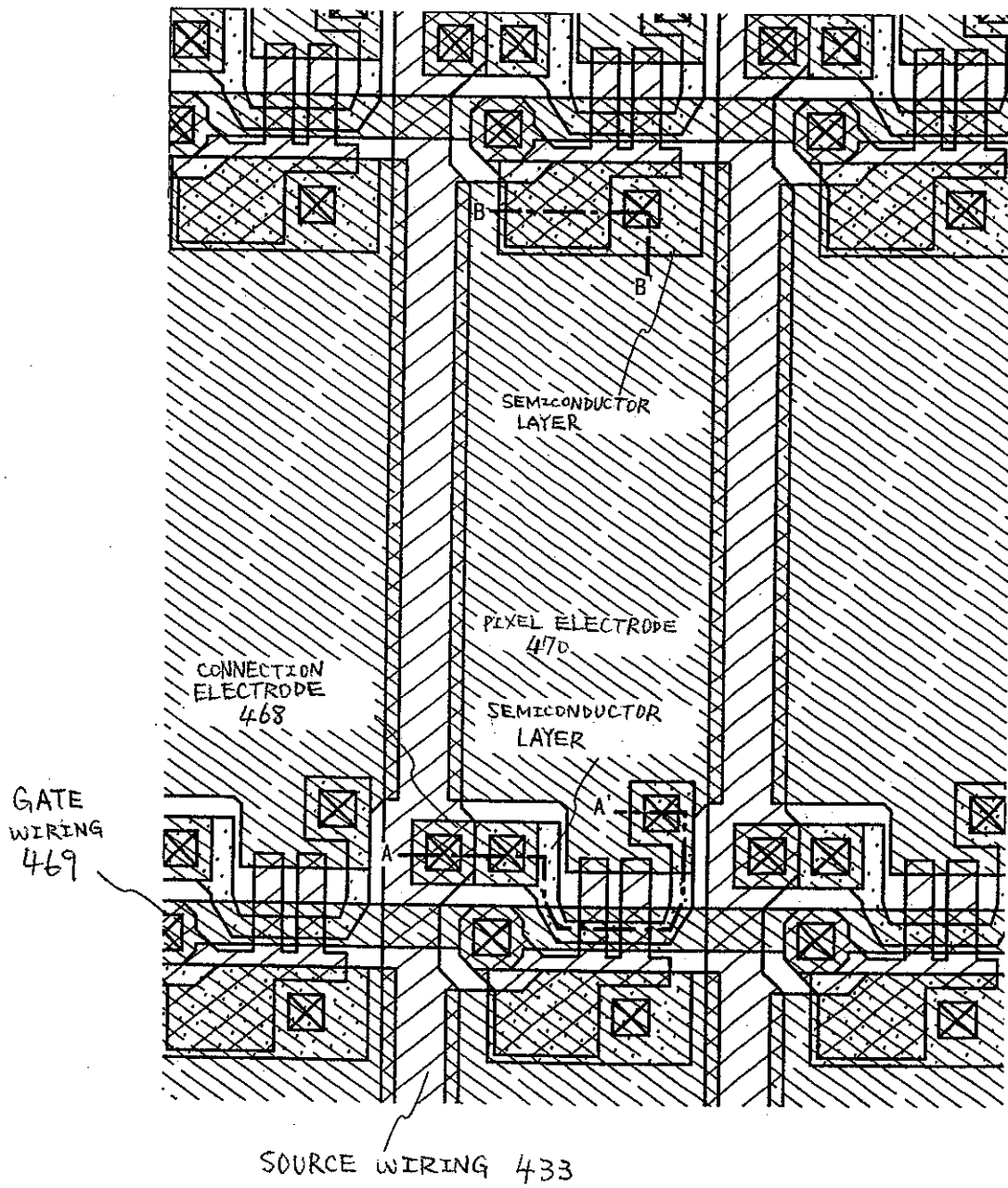


Fig. 10

Fig. 11



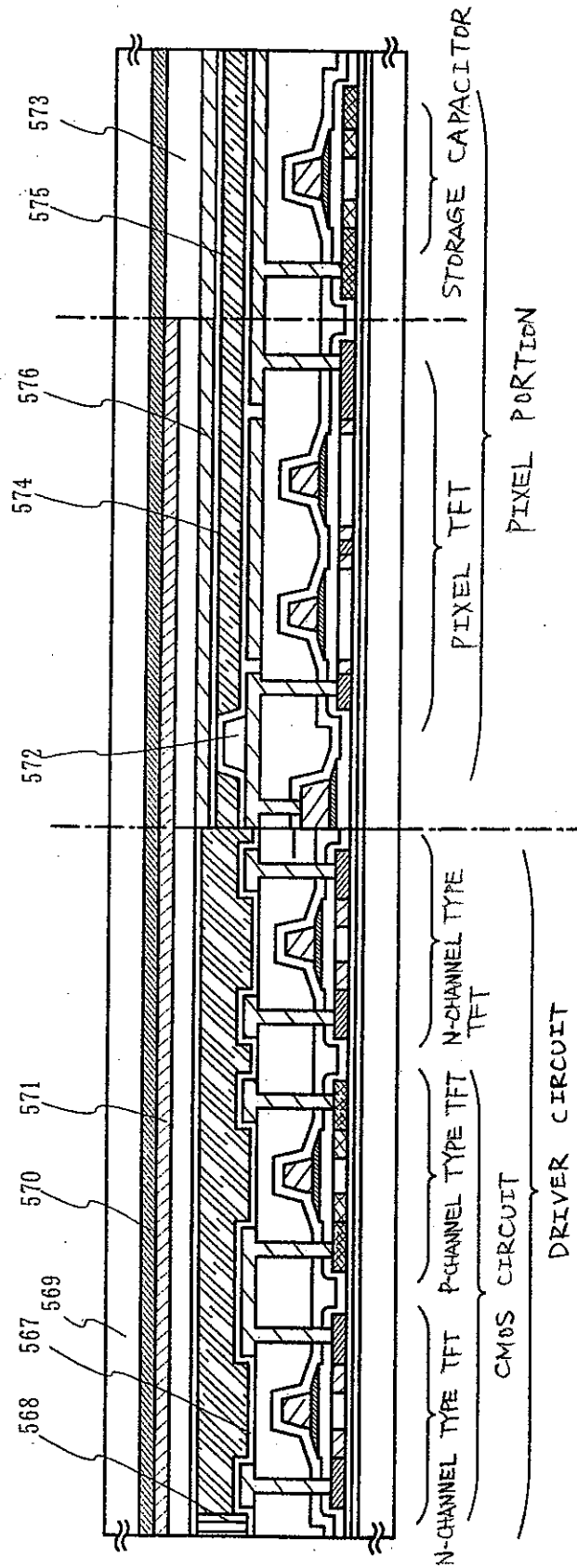


Fig. 12

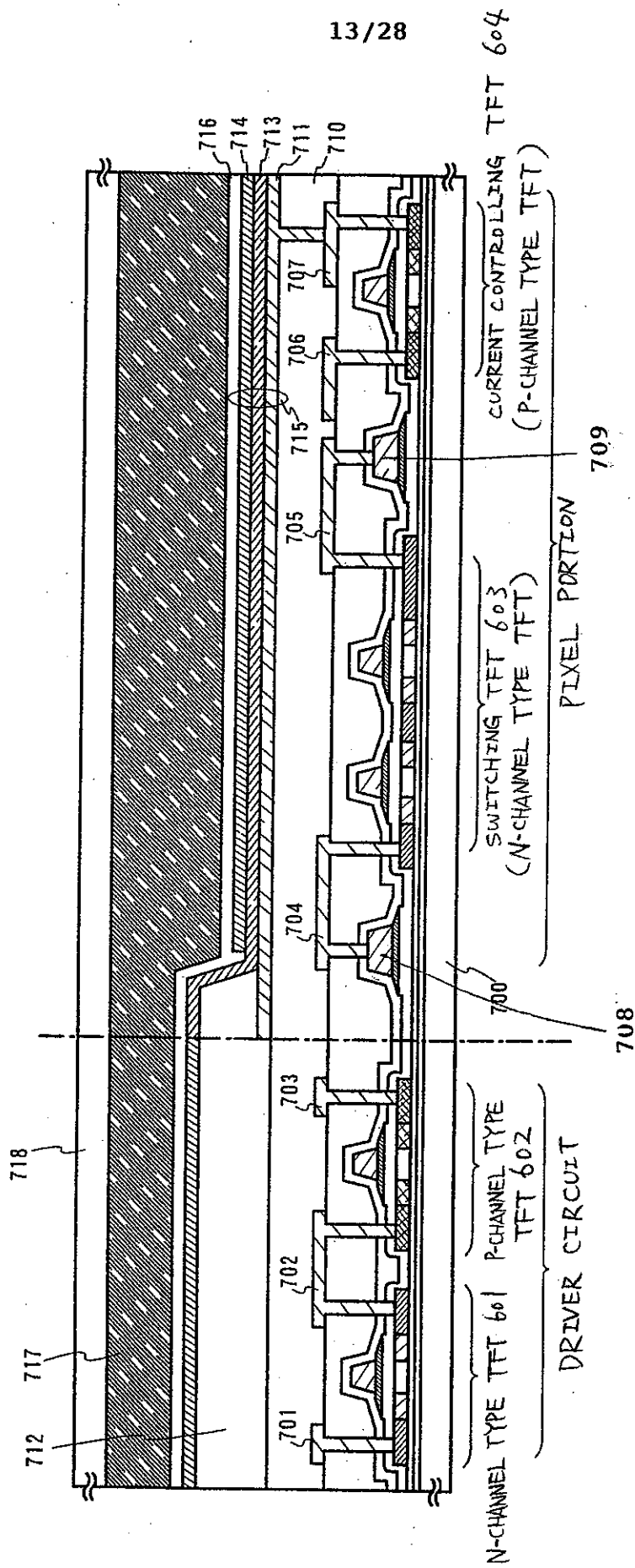
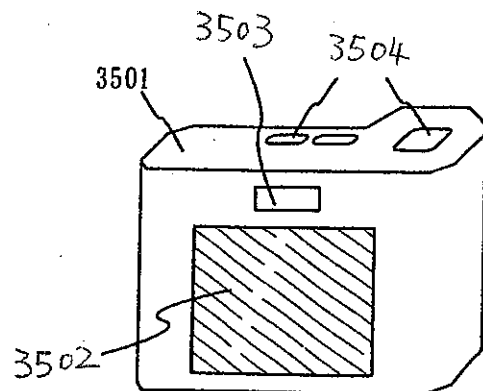
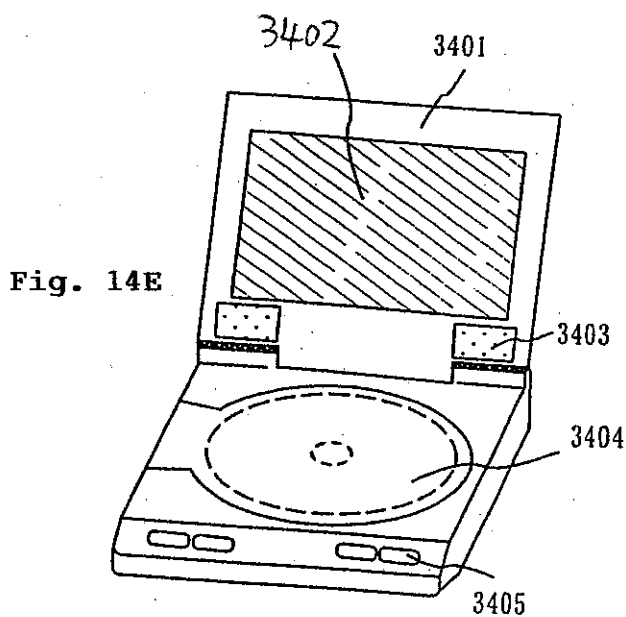
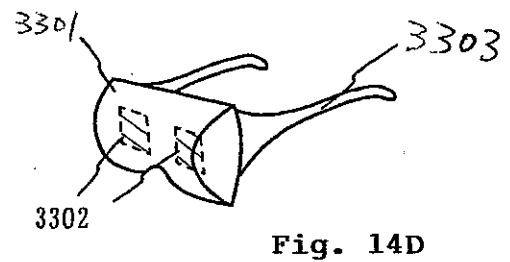
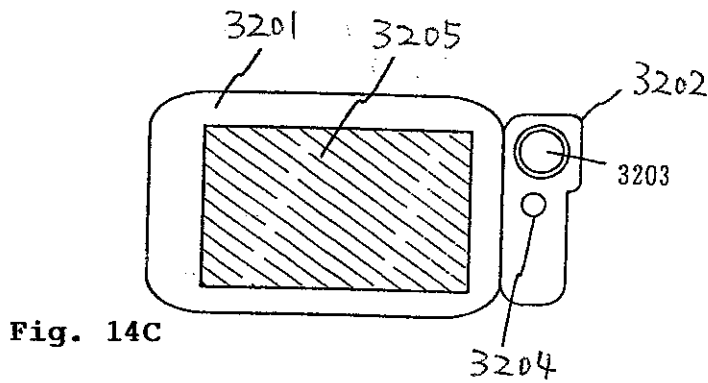
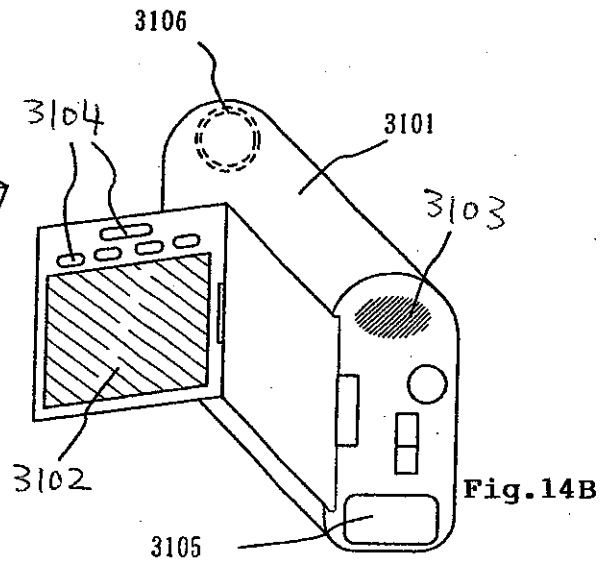
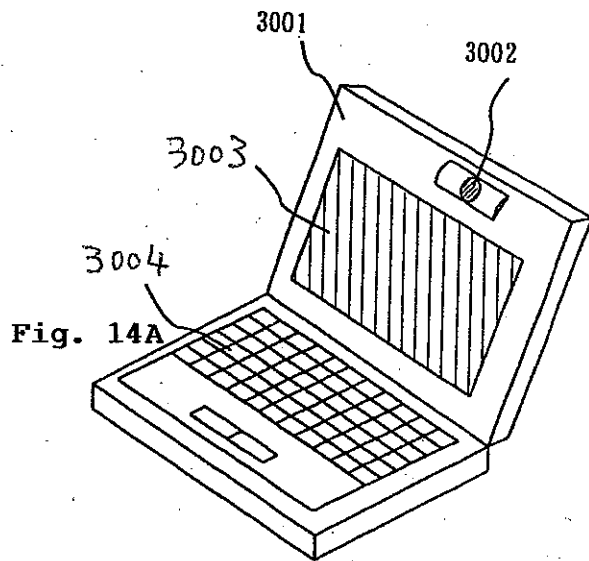


Fig. 13



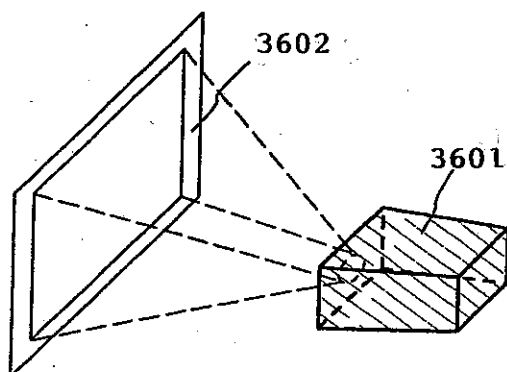


Fig. 15A

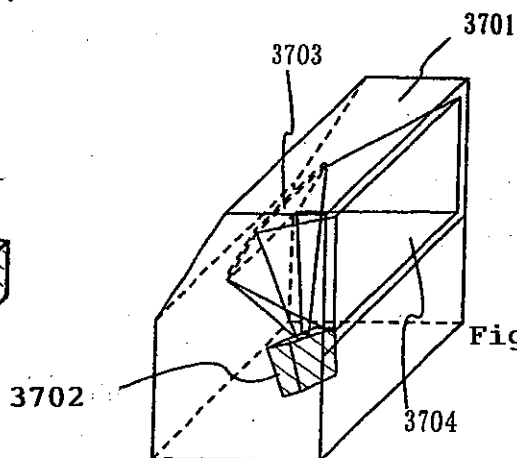


Fig. 15B

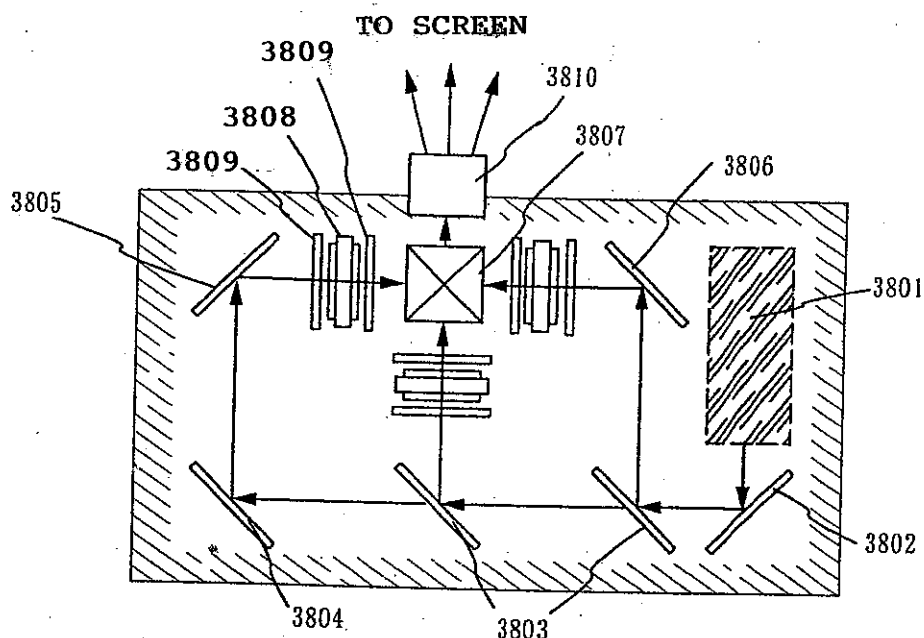


Fig. 15C PROJECTION DEVICE (THREE PLATE TYPE)

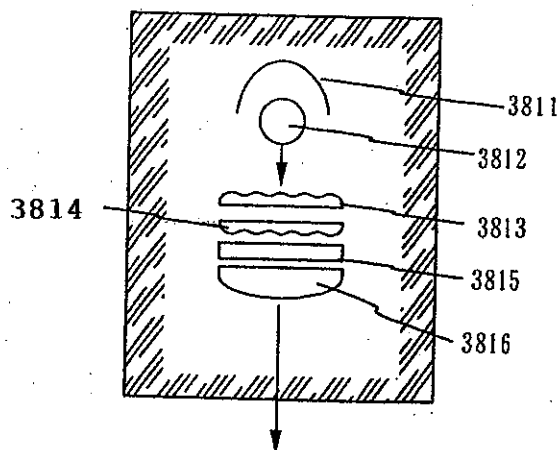
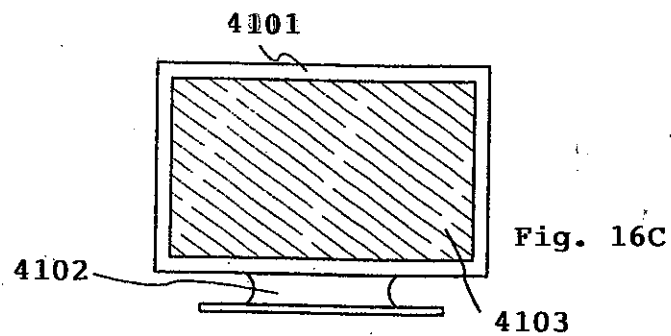
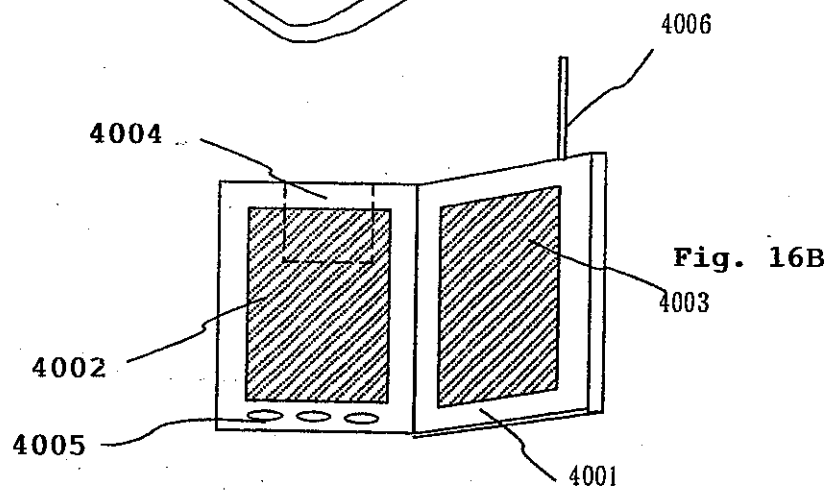
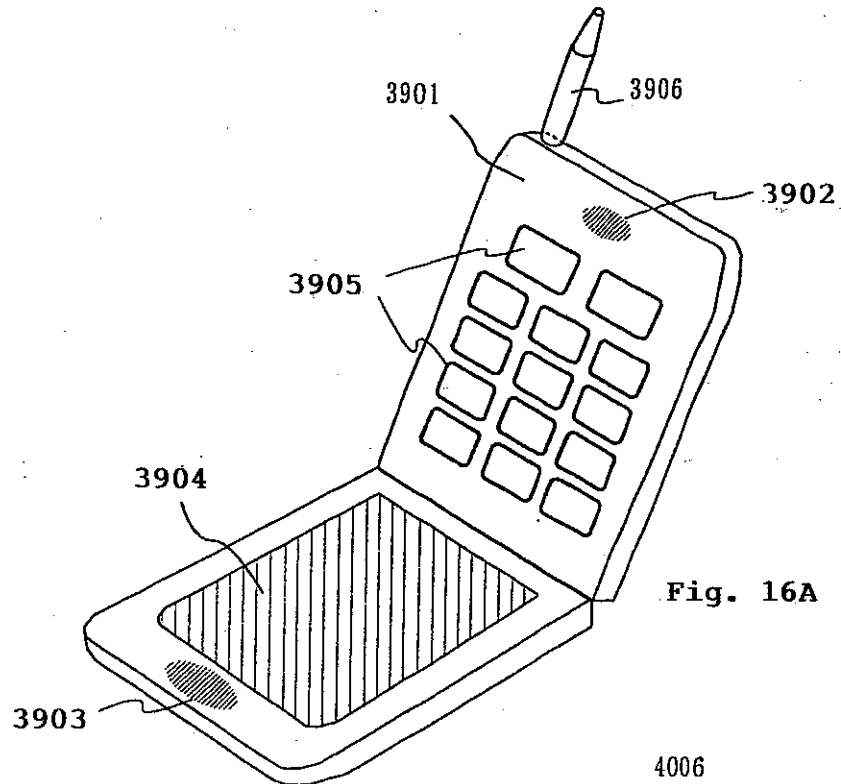


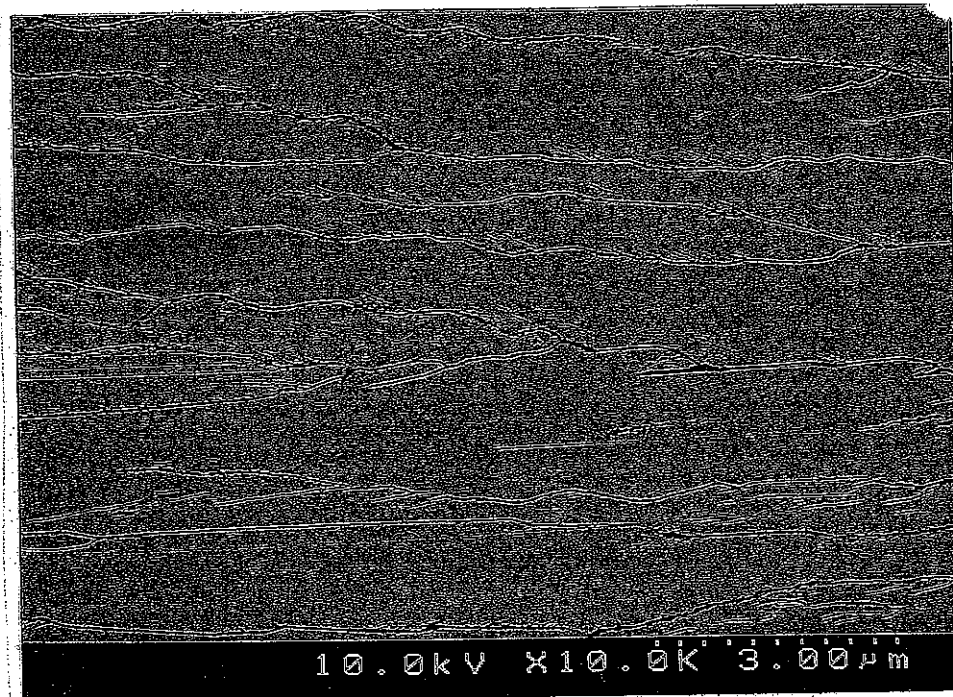
Fig. 15D LIGHT SOURCE OPTICAL SYSTEM





→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.17



→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.18

Fig. 19A FORMATION OF BASE INSULATING FILM/
FORMATION OF SEMICONDUCTOR FILM

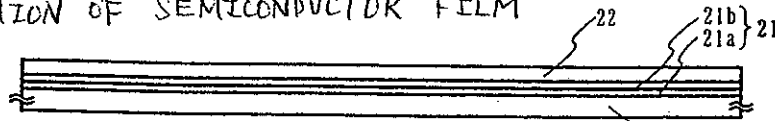


Fig. 19B CRYSTALLIZATION OF SEMICONDUCTOR FILM



Fig. 19c FIRST DOPING PROCESS

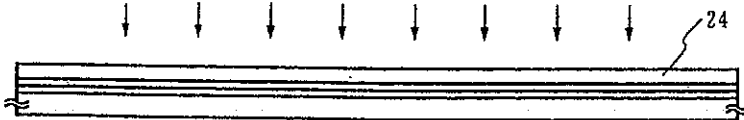


Fig. 19D FIRST ETCHING PROCESS/FORMATION OF INSULATING FILM/
FORMATION OF CONDUCTIVE FILM

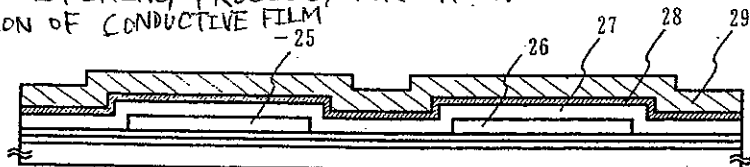


Fig. 19E SECOND ETCHING PROCESS/SECOND DOPING PROCESS

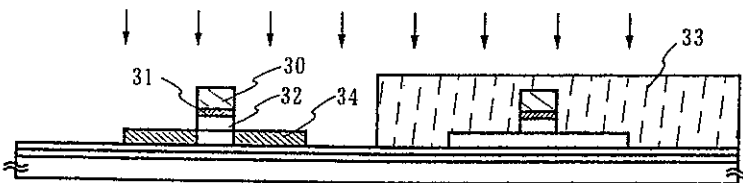


Fig. 19F THIRD DOPING PROCESS

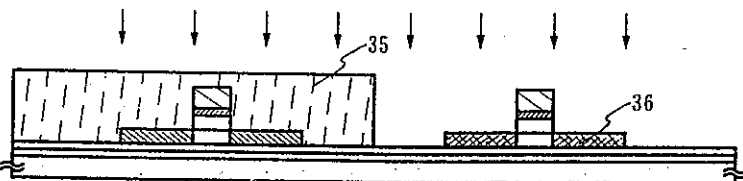


Fig. 19G FORMATION OF FIRST INTERLAYER INSULATING FILM/
HEAT TREATMENT

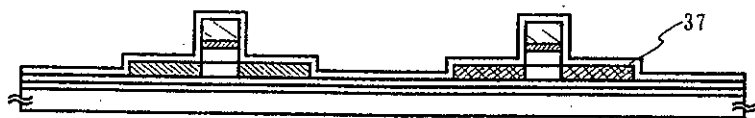
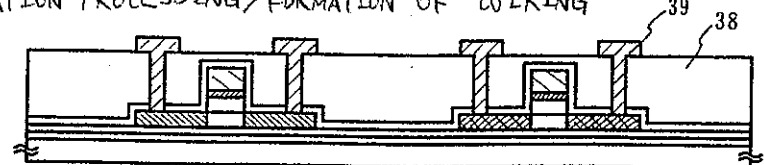


Fig. 19H FORMATION OF SECOND INTERLAYER INSULATING FILM/
HYDROGENATION PROCESSING/FORMATION OF WIRING



N-CHANNEL TYPE TFT 51

P-CHANNEL TYPE TFT 52

Fig.20A

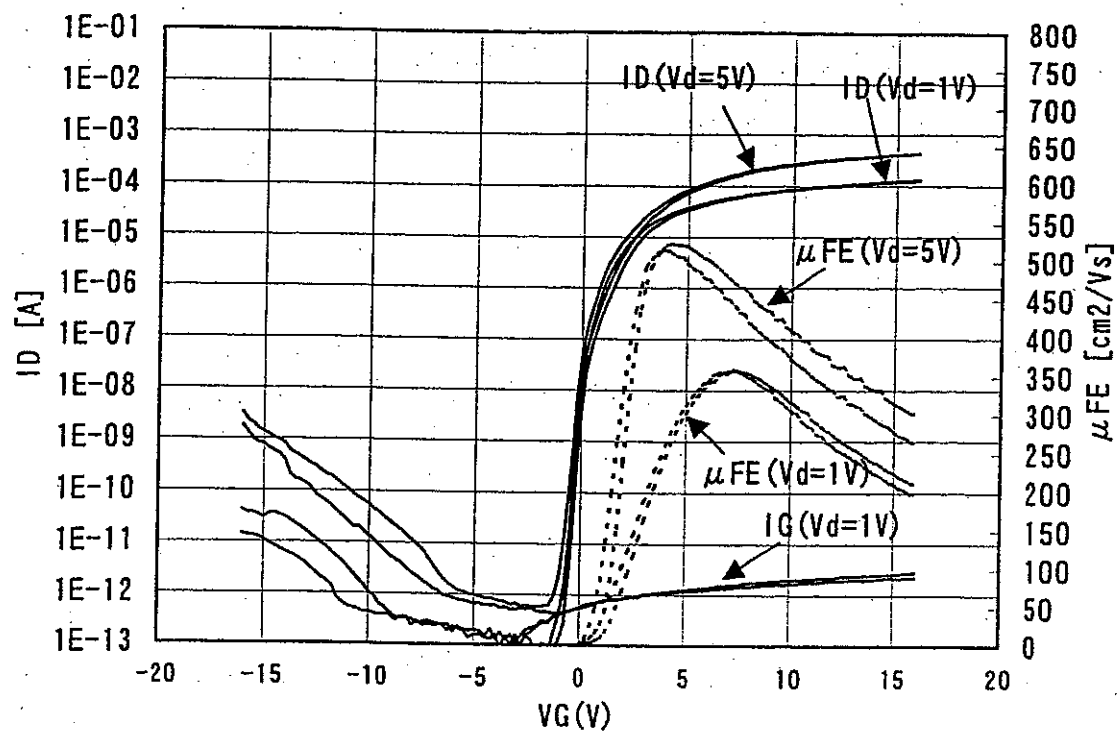
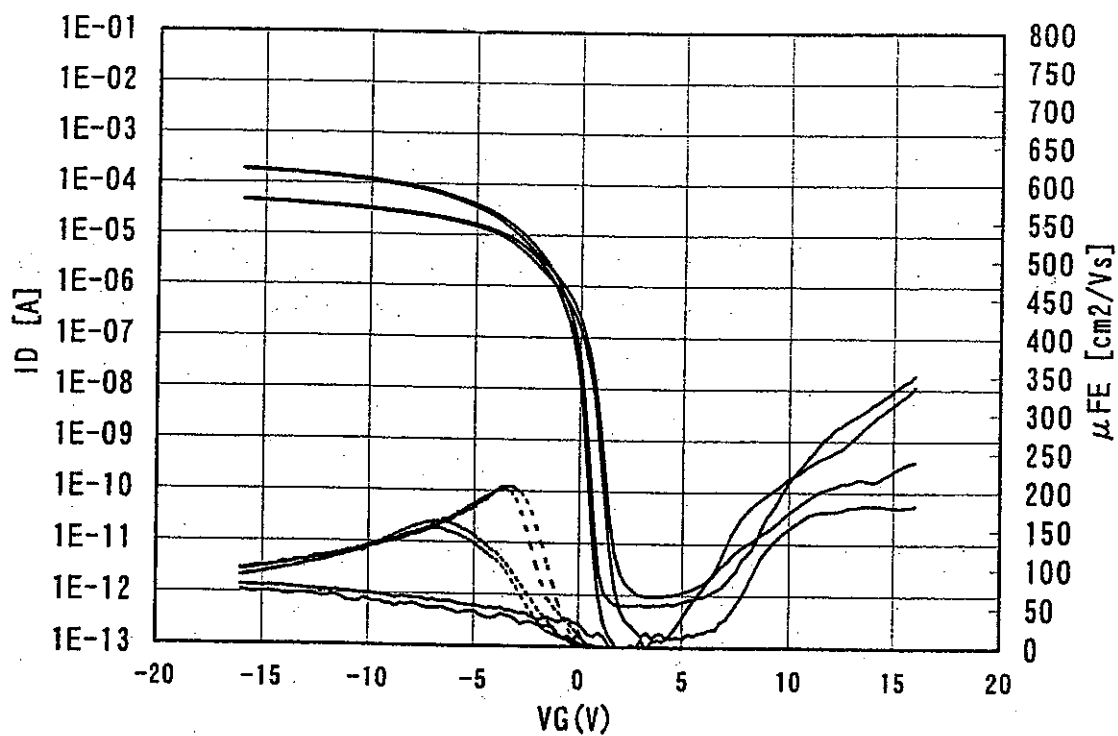


Fig. 20B



FORMATION OF METAL CONTAINING LAYER

Fig. 21A

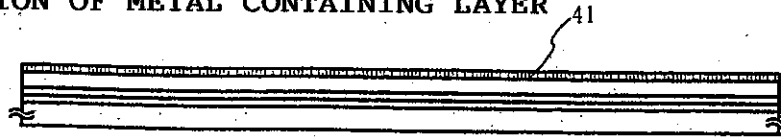


Fig. 21B

HEAT TREATMENT

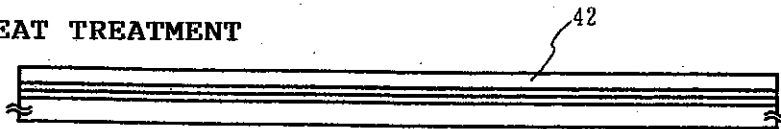


Fig. 21C

LASER ANNEALING

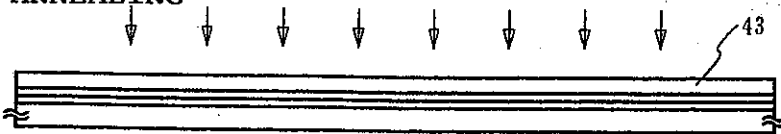


Fig. 22A

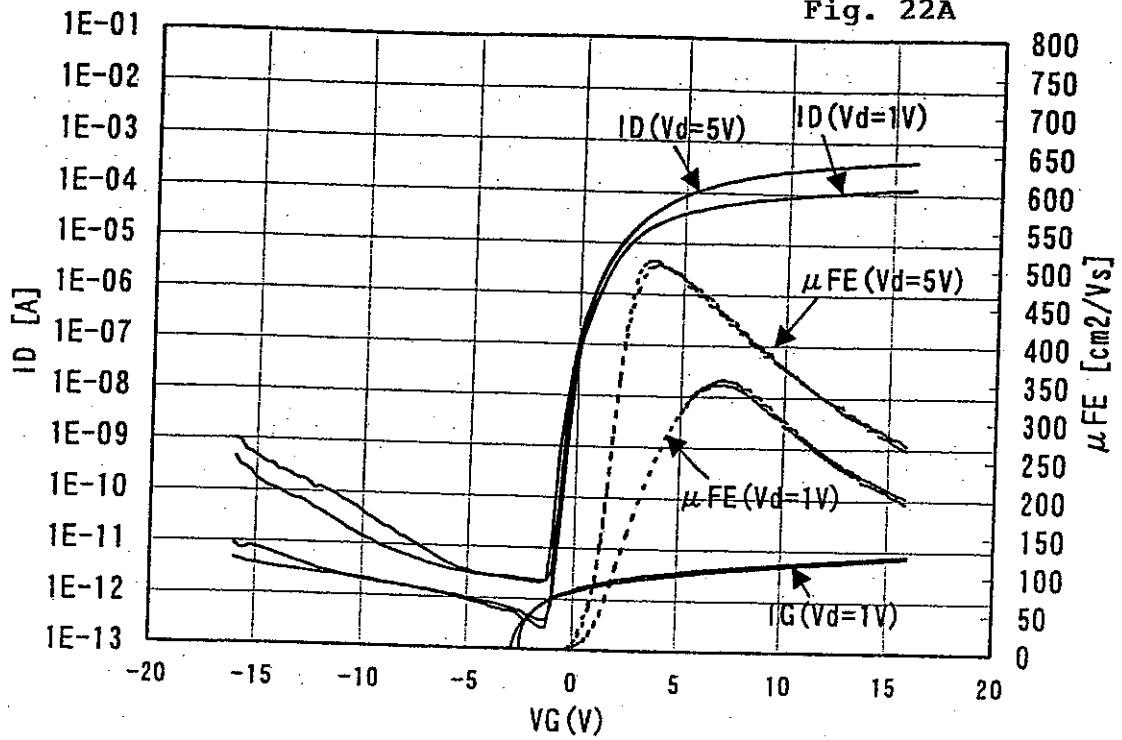


Fig. 22B

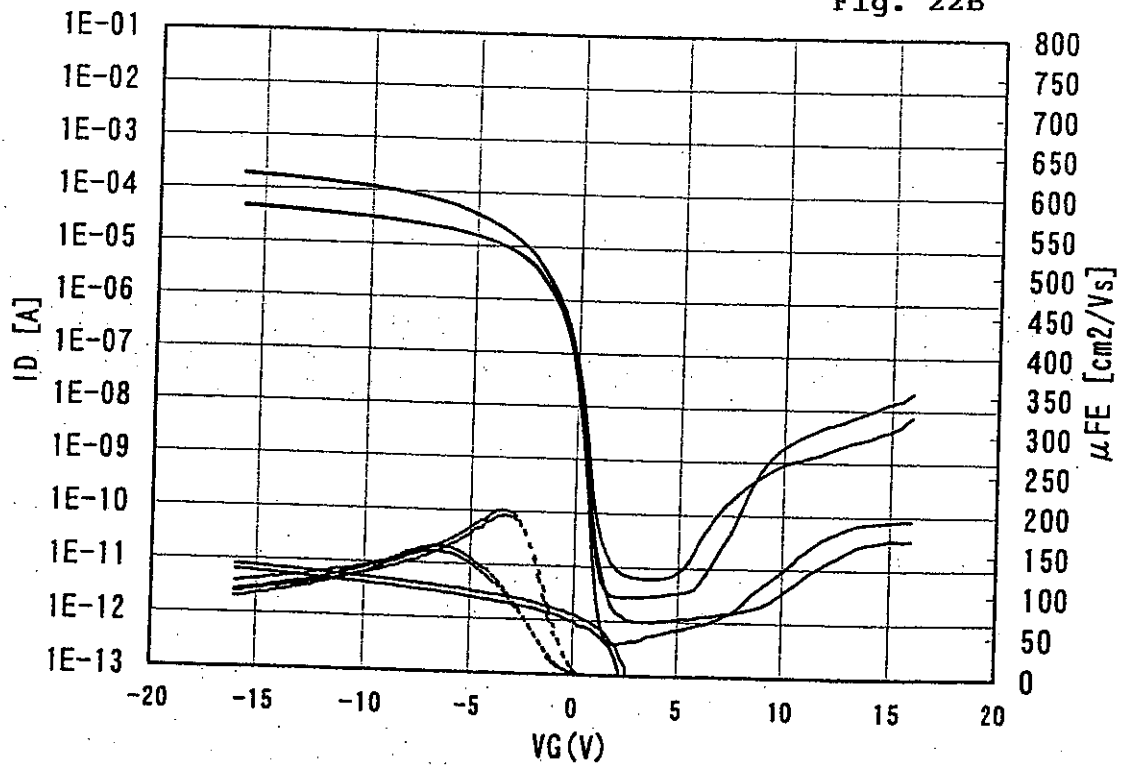


Fig. 23A

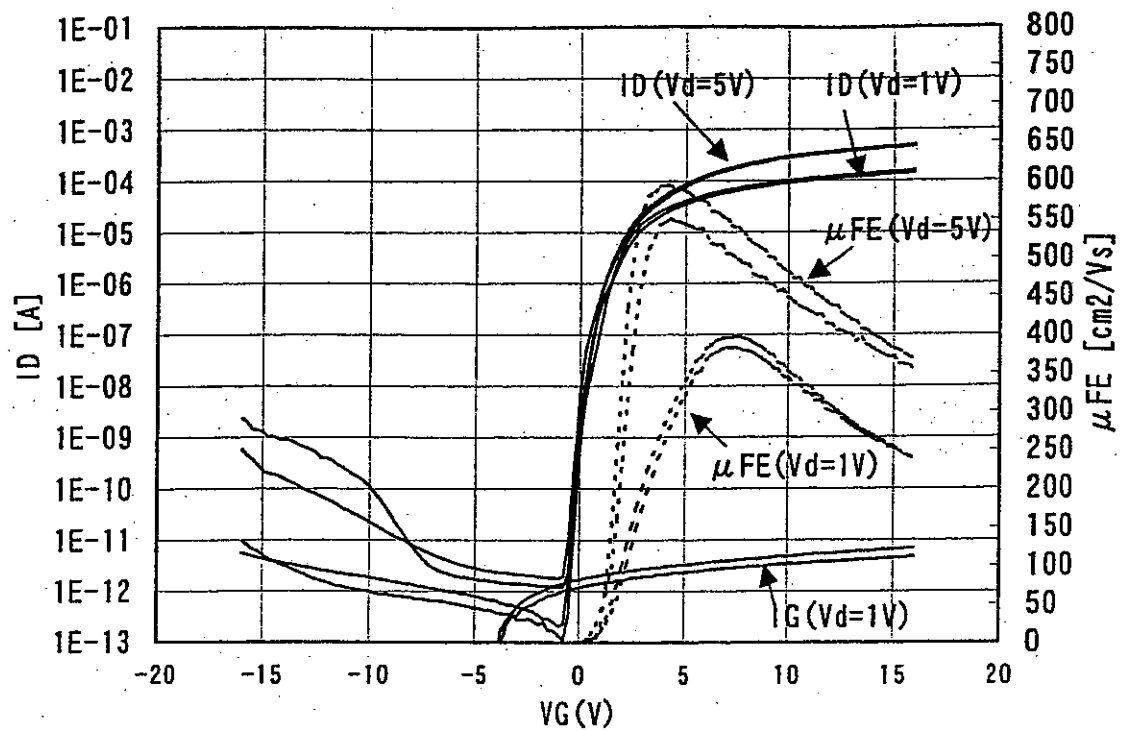
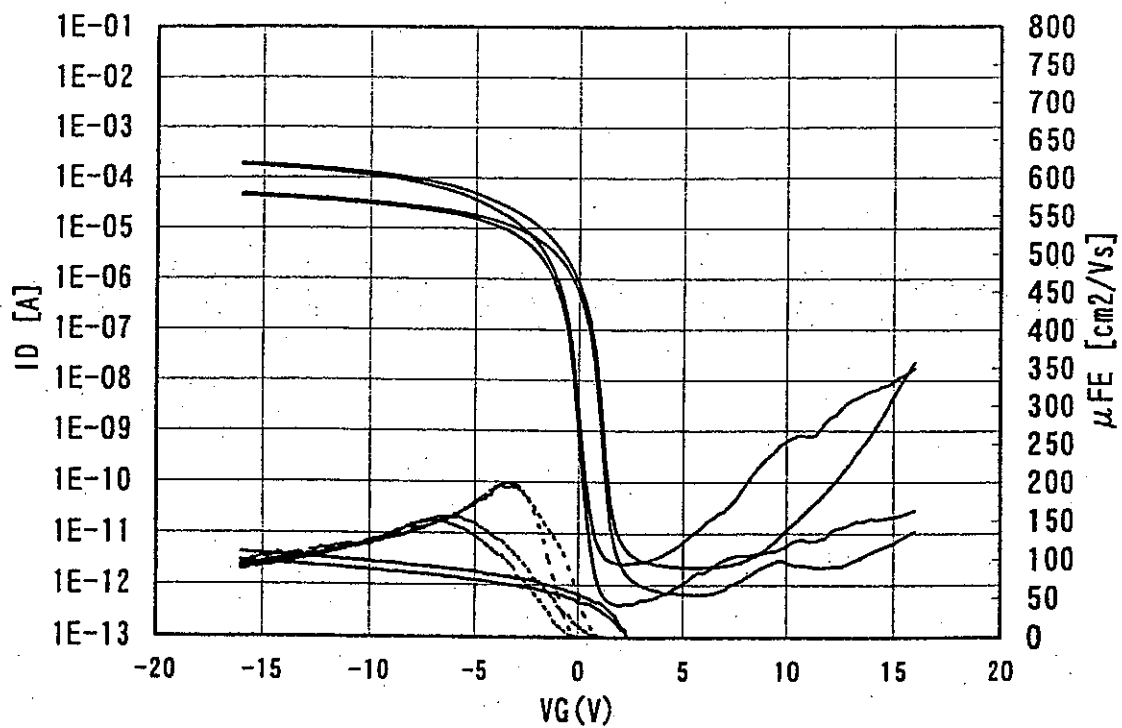


Fig. 23B



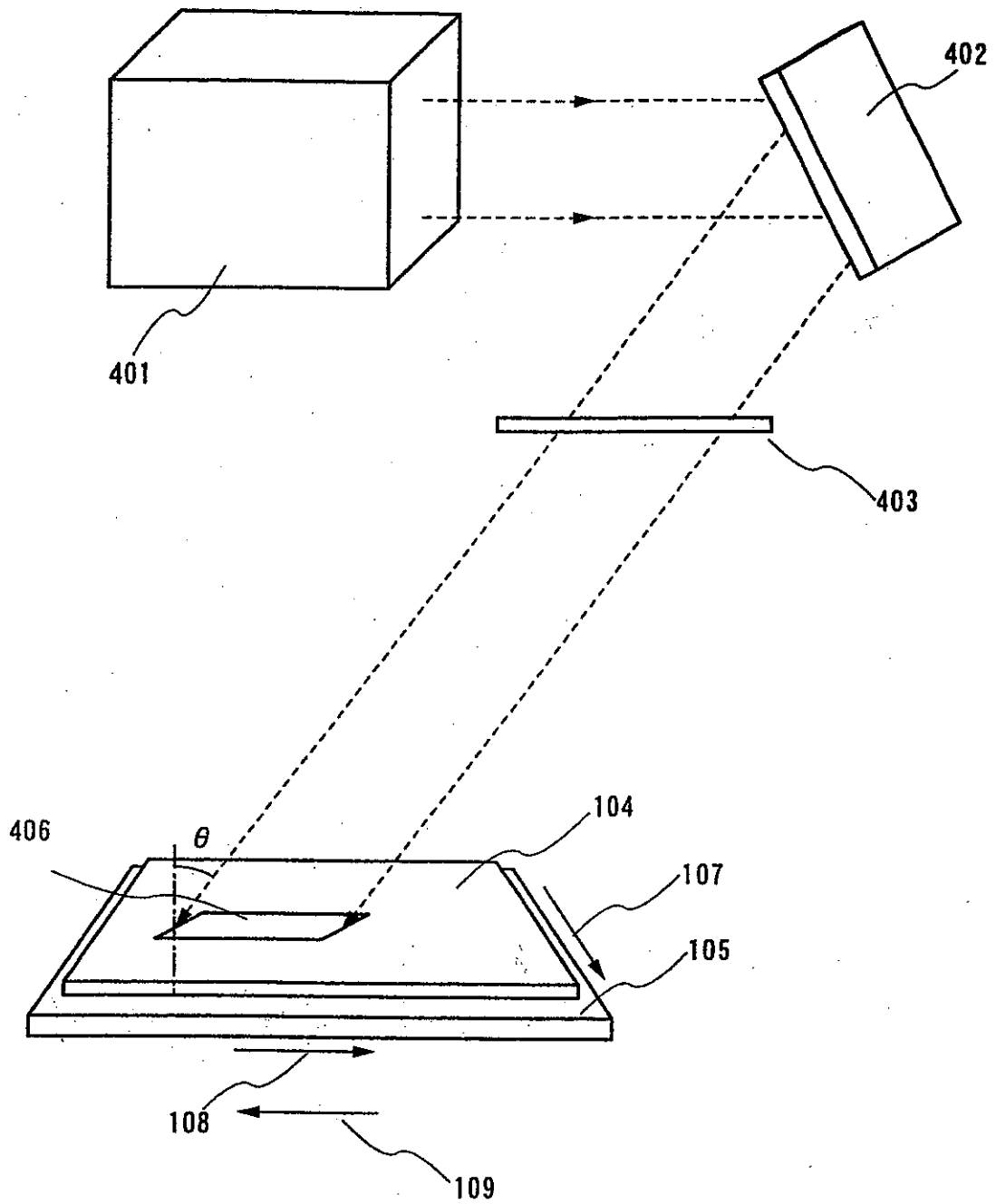
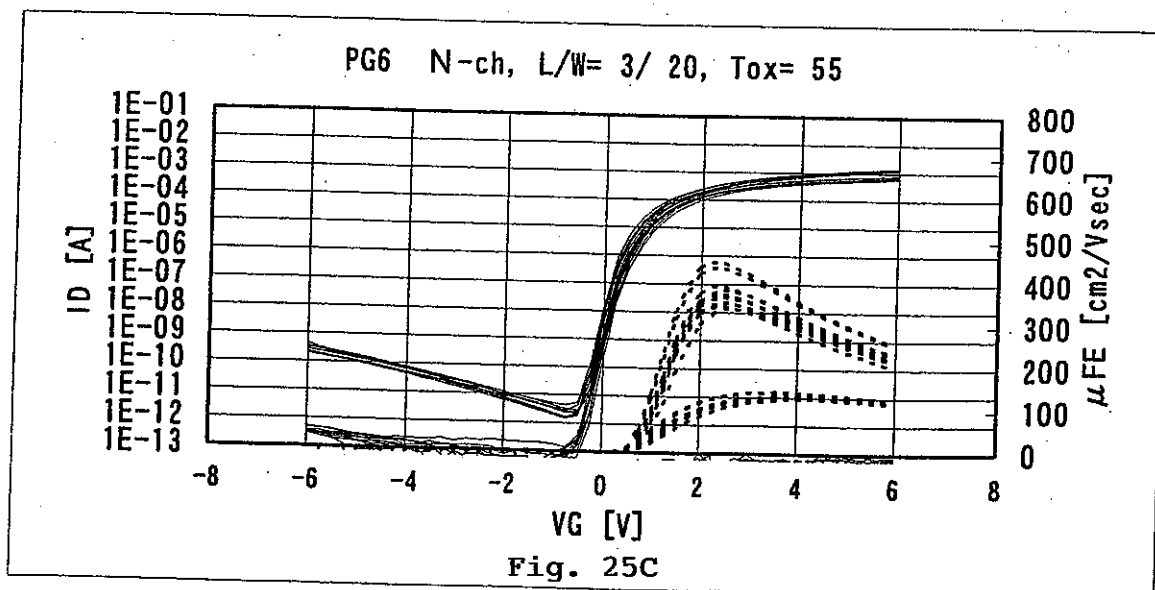
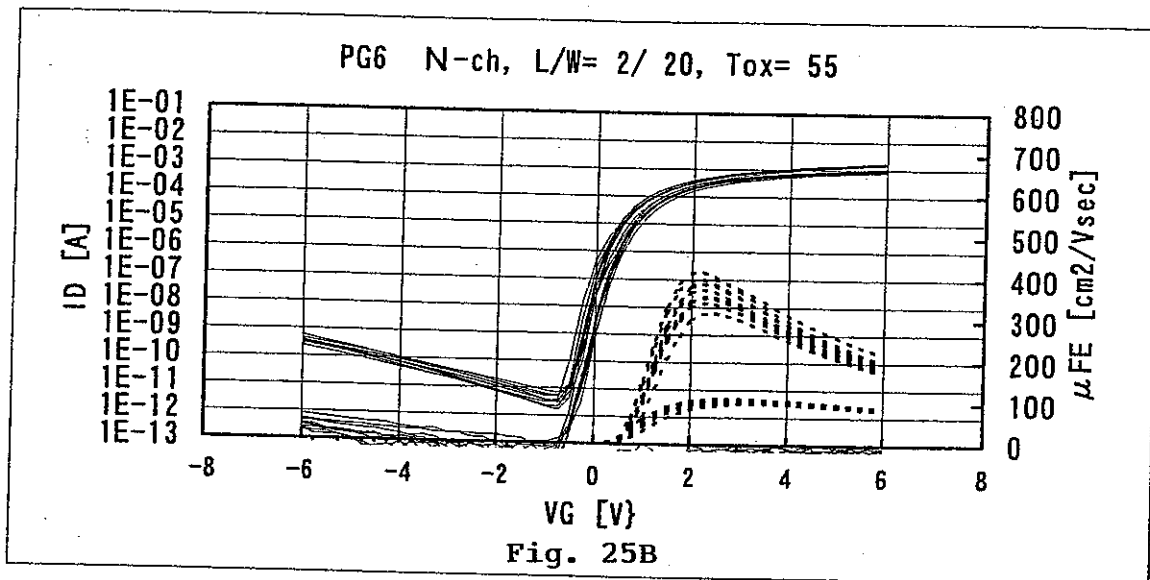
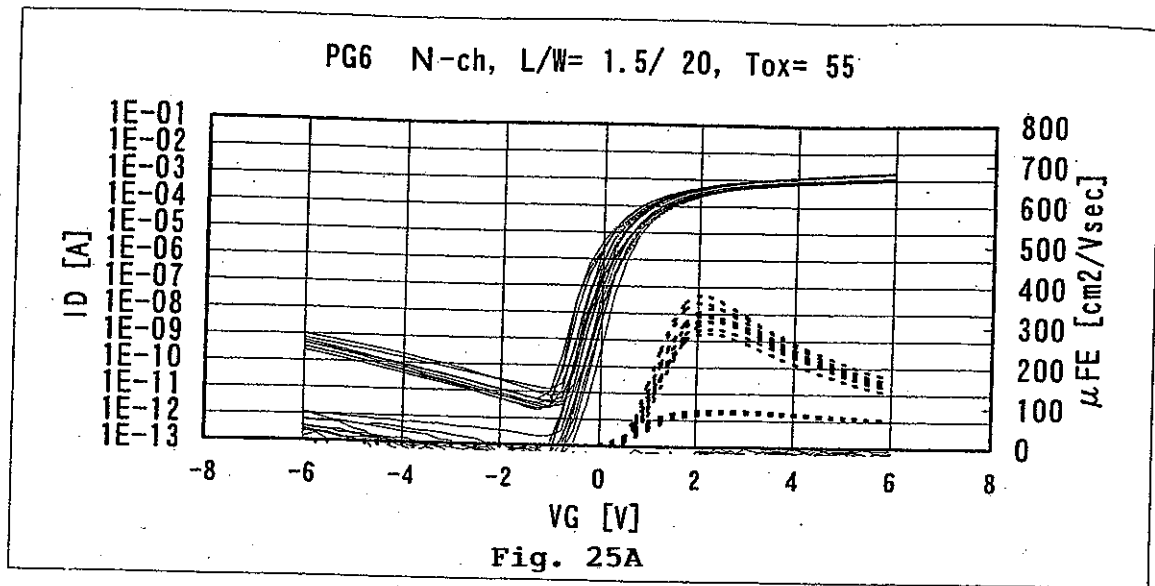
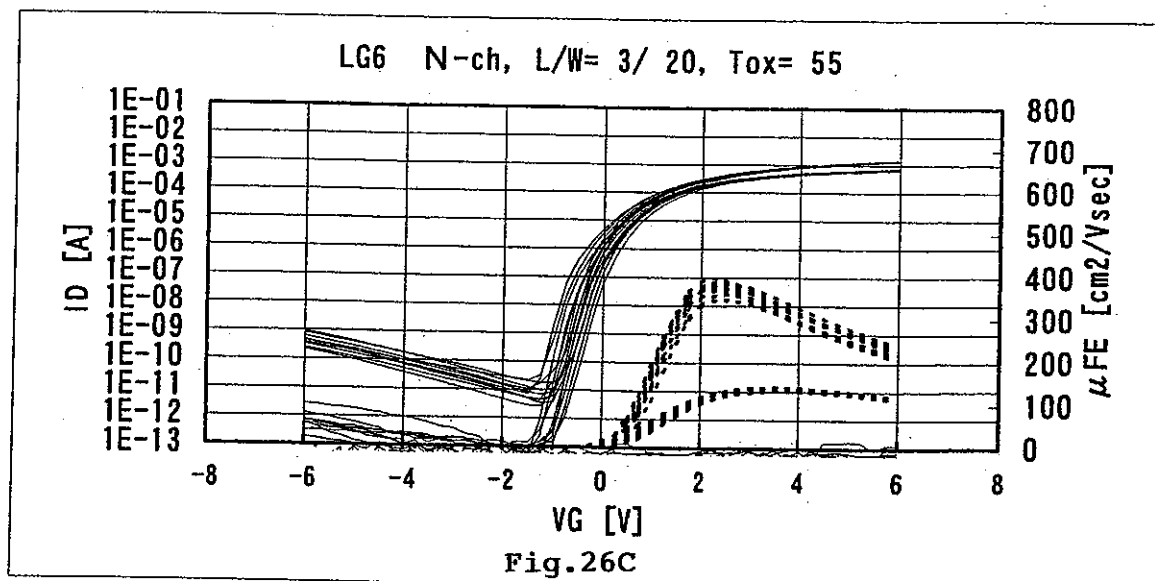
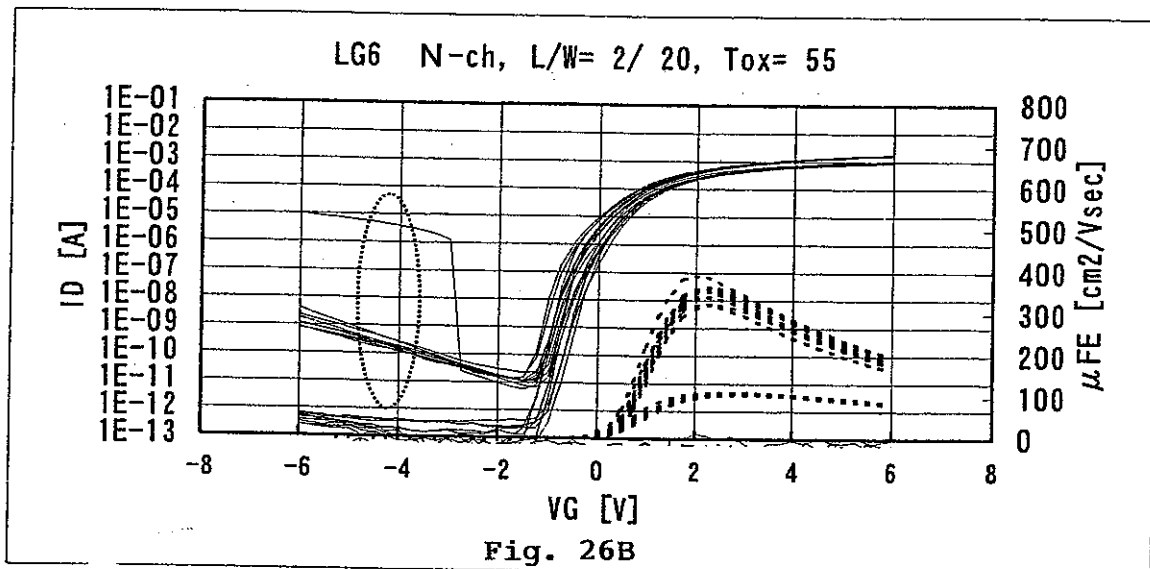
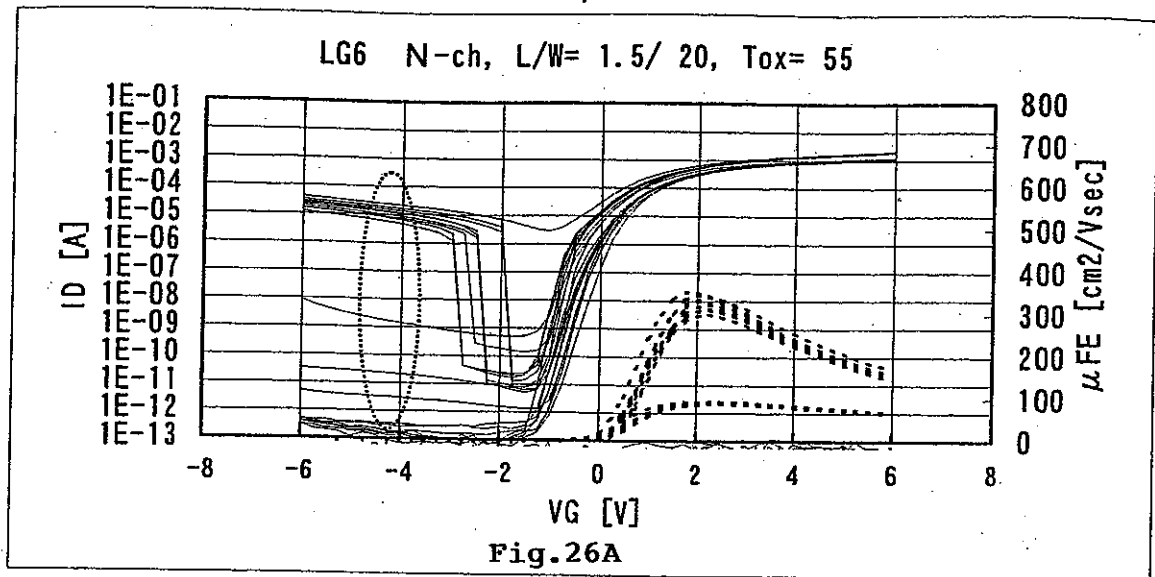


Fig. 24





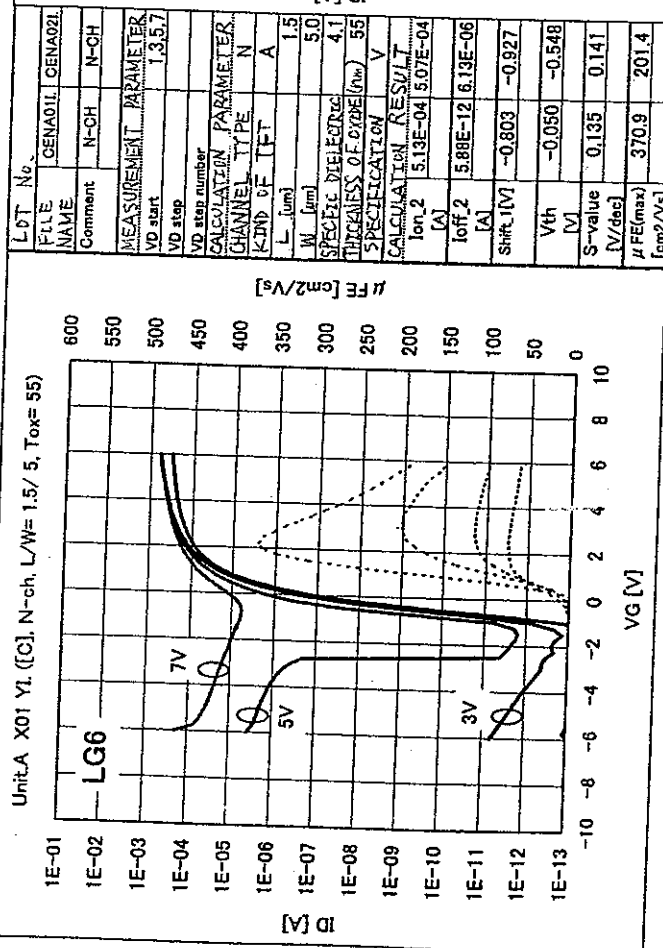
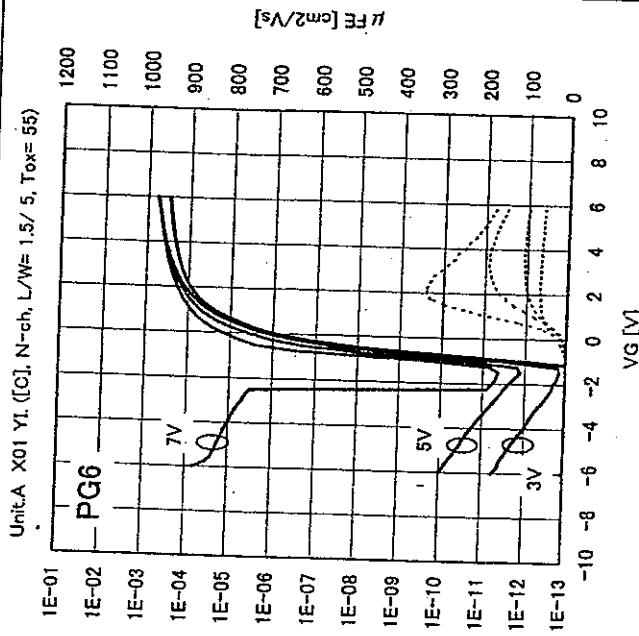
 $L/W=1.25/5\mu m$

Fig.27
COMPLETE DEPLETION TYPE (THICKNESS OF SEMICONDUCTOR FILM IS 66nm)

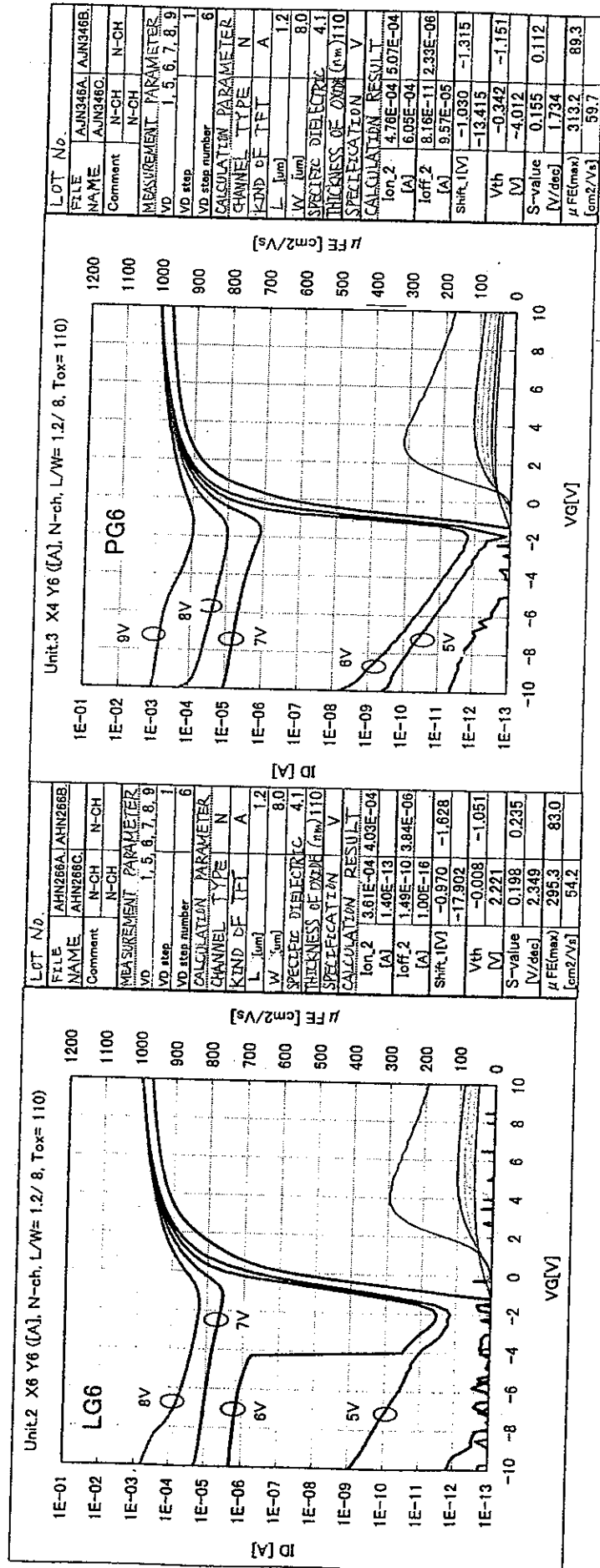


Fig.28

PARTIAL DEPLETION TYPE (THICKNESS OF SEMICONDUCTOR FILM IS 150nm)